



# Quantum dot thermometry at ultra-low temperature in a dilution refrigerator with a $^4\text{He}$ immersion cell

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ABSTRACT

FULL TEXT

FIGURES

TOOLS

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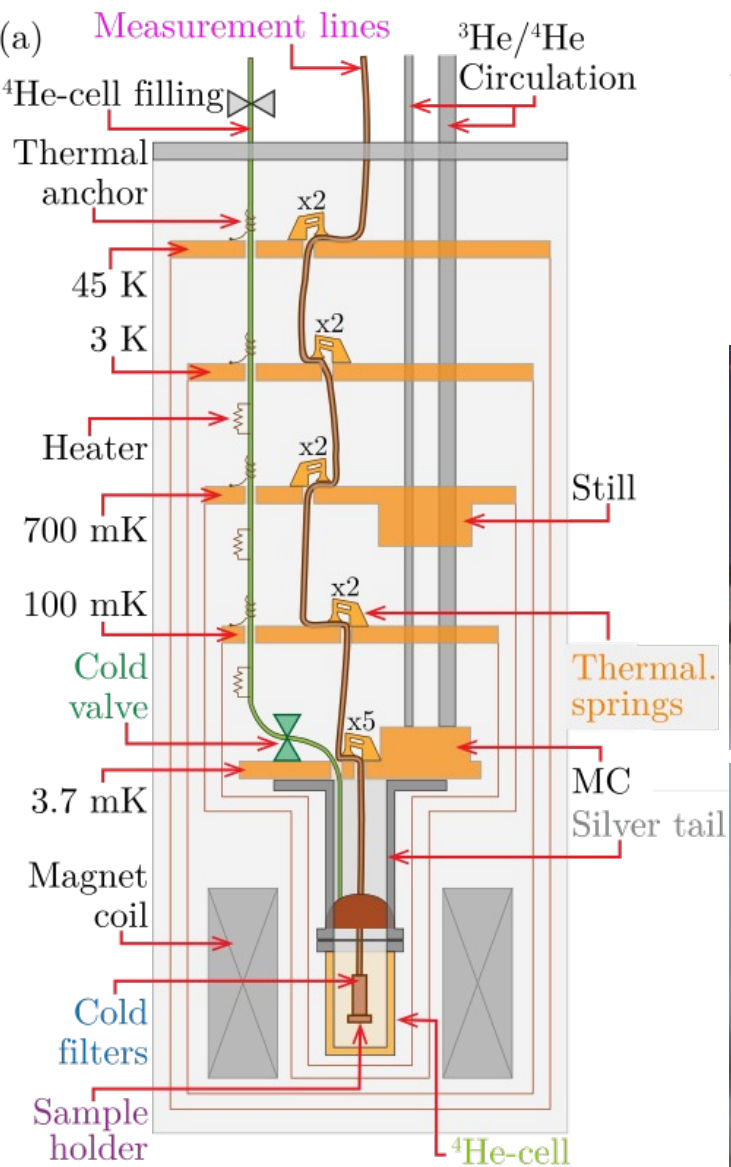
METRICS

## TOPICS

- Two-dimensional electron gas
- Temperature metrology
- Amplifiers
- Quantum dots
- Dilution refrigerators
- Superfluids

## ABSTRACT

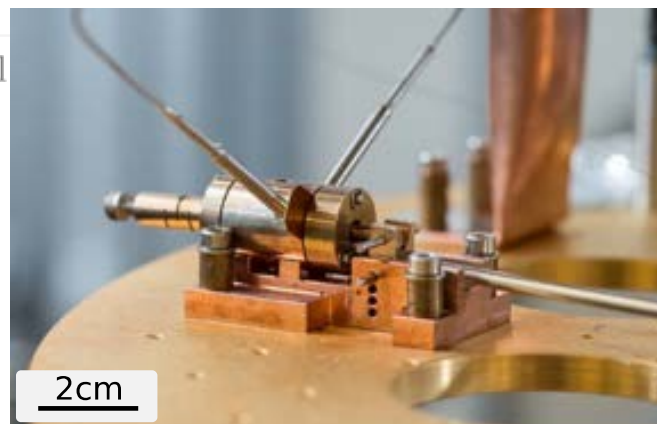
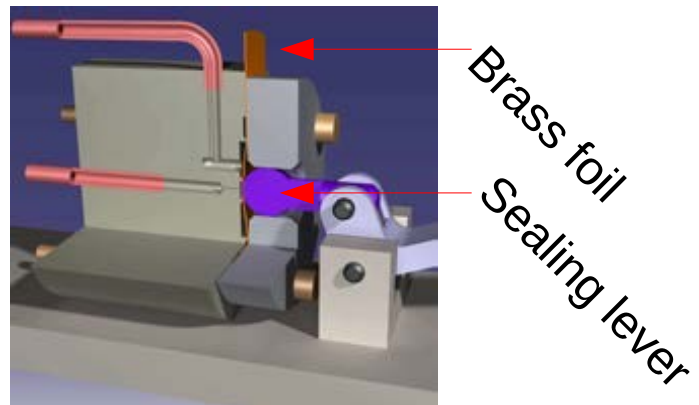
Experiments performed at a temperature of a few millikelvins require effective thermalization schemes, low-pass filtering of the measurement lines, and low-noise electronics. Here, we report on the modifications to a commercial dilution refrigerator with a base temperature of 3.5 mK that enable us to lower the electron temperature to 6.7 mK measured from the Coulomb peak width of a quantum dot gate-defined in an  $\text{AlGaAs}$

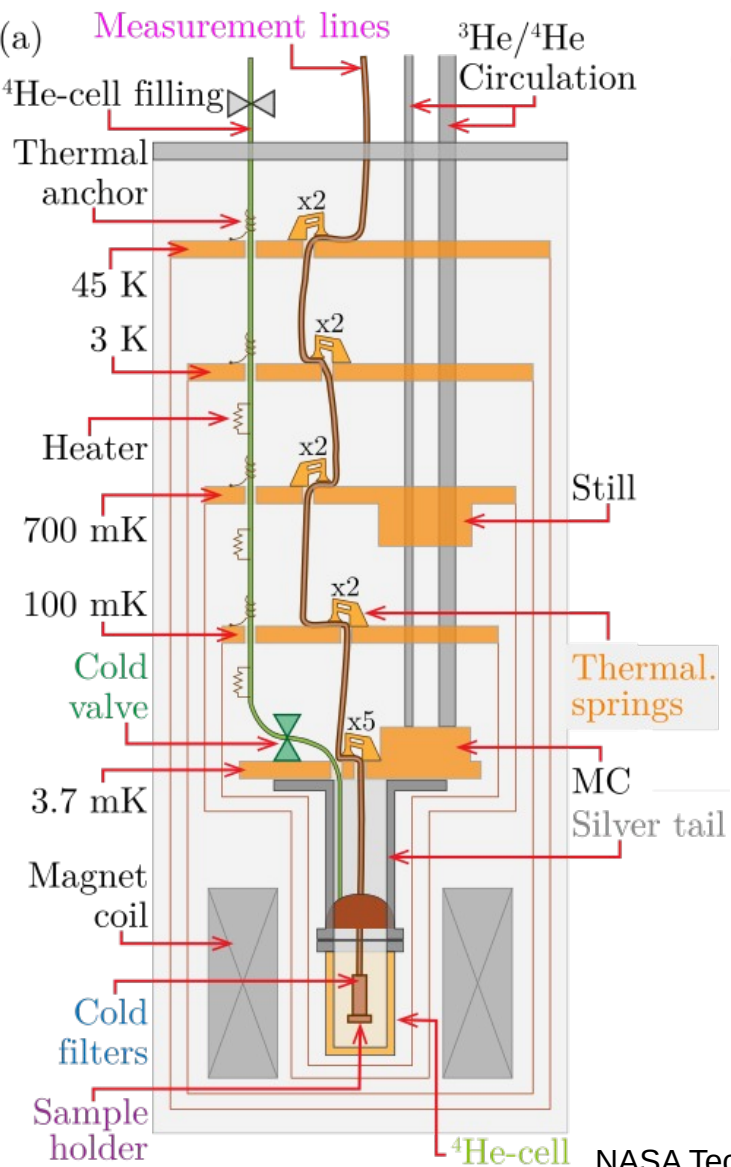


# A. The Immersion Cell

At 2.2K <sup>4</sup>He phase-transitions to super-fluid

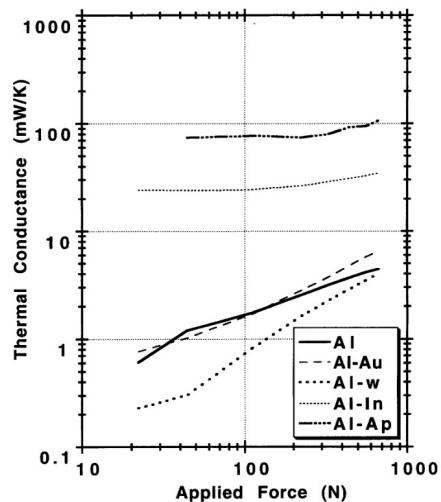
- No temperature gradient (good)
- No viscosity (bad)



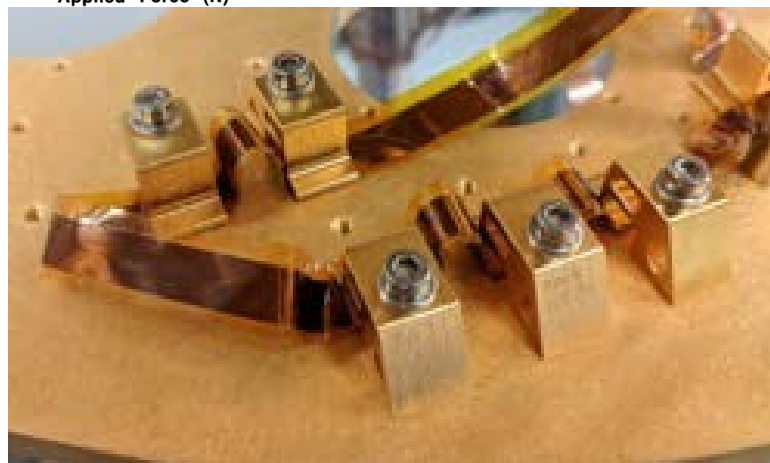


## C. Measurement Lines

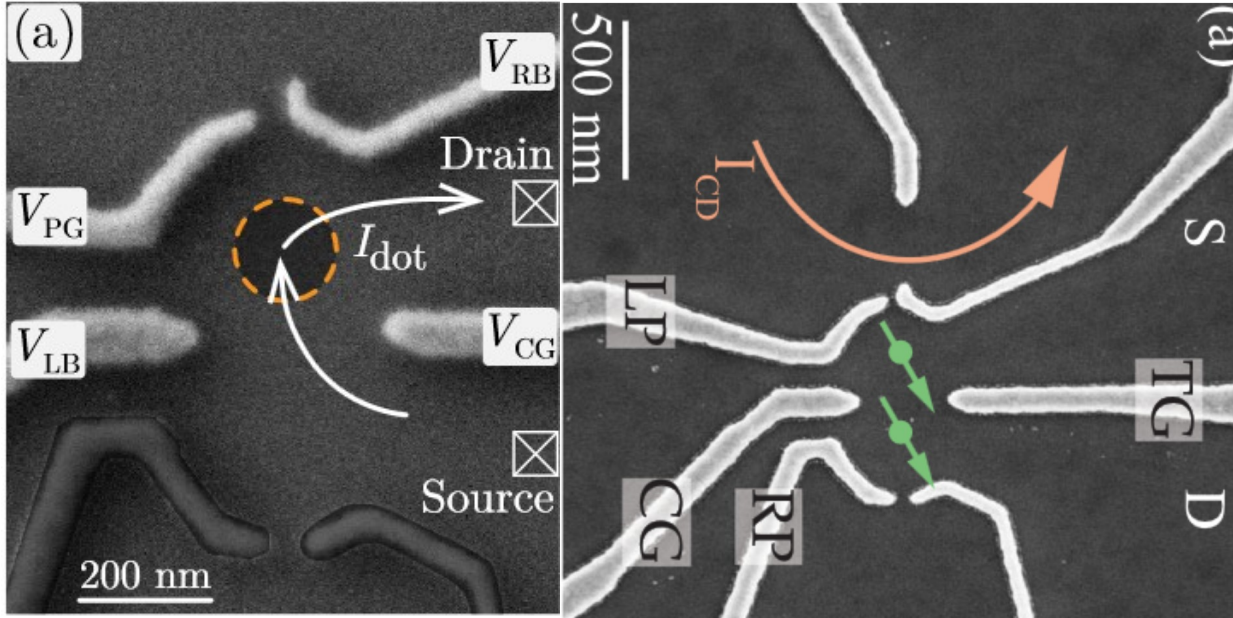
Replace coaxial wires with flat-band wires



Applies  
500N



### III. Quantum Dot Thermometry



GaAs/AlGaAs heterostructure 2DEG depleted to the last dot

Quantum dot thermometry:

i. conduction through the dot in a single level

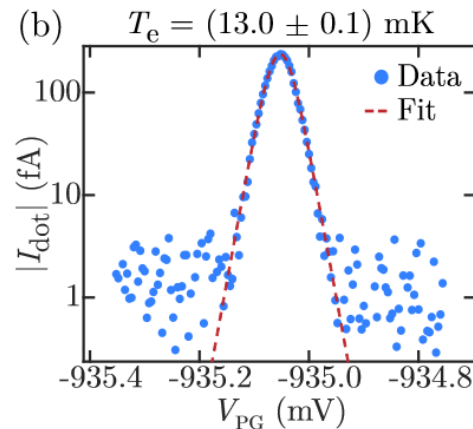
ii. tunnel coupling broadening

$$\Gamma \ll k_B T$$

iii. small source-drain bias

$$eV_{sd} < 4k_B T$$

=> Small dot, low occupation number



$$I_{dot} = \frac{I_0}{\cosh [\alpha e (V_{PG} - V_0) / 2k_B T]}$$

# S1. Standard DC Measurement. $T_e=13.0\text{mK}$

ETH In-house IV Converter  
8nV/ $\sqrt{\text{Hz}}$  @ 33Hz input noise

BasPI IV Converter  
2nV/ $\sqrt{\text{Hz}}$  @ 10Hz input noise



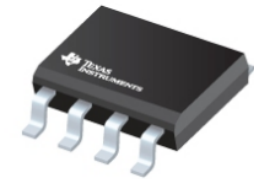
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OPA140 ✓ ACTIVE

11MHz, Single Supply, Low Noise, Preci

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## Features

- Very-Low Offset Drift: 1  $\mu\text{V}/^\circ\text{C}$  maximum
- Very-Low Offset: 120  $\mu\text{V}$
- Low Input Bias Current: 10 pA maximum
- Very-Low 1/f Noise: 250 nV<sub>pp</sub>, 0.1 Hz to 10 Hz
- Low Noise: 5.1 nV/ $\sqrt{\text{Hz}}$
- Slew Rate: 20 V/ $\mu\text{s}$
- Low Supply Current: 2 mA maximum
- Input Voltage Range Includes V<sub>-</sub> supply
- Single-Supply Operation: 4.5 V to 36 V
- Dual-Supply Operation:  $\pm 2.25$  V to  $\pm 18$  V
- No Phase Reversal
- Industry-Standard SOIC Packages
- VSSOP, TSSOP, and SOT-23 Packages

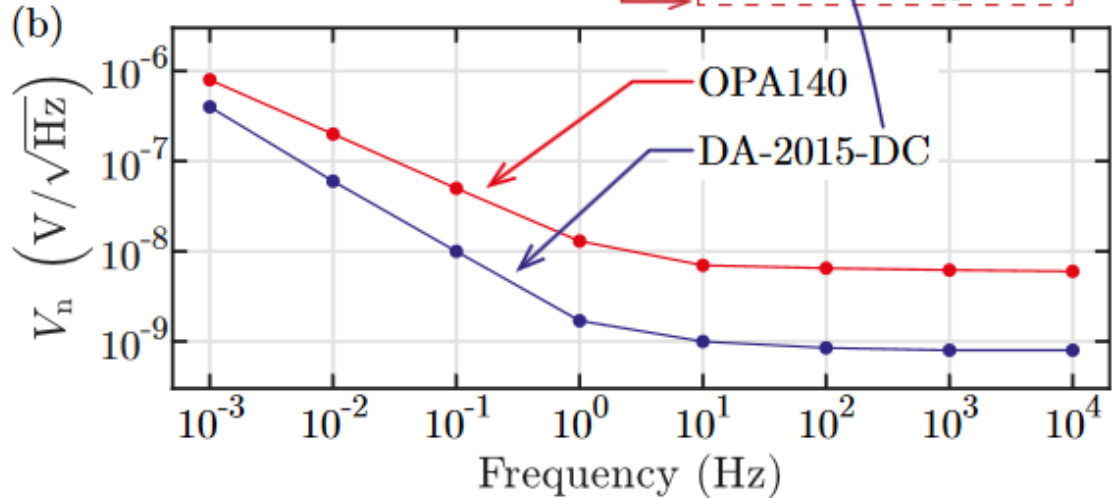
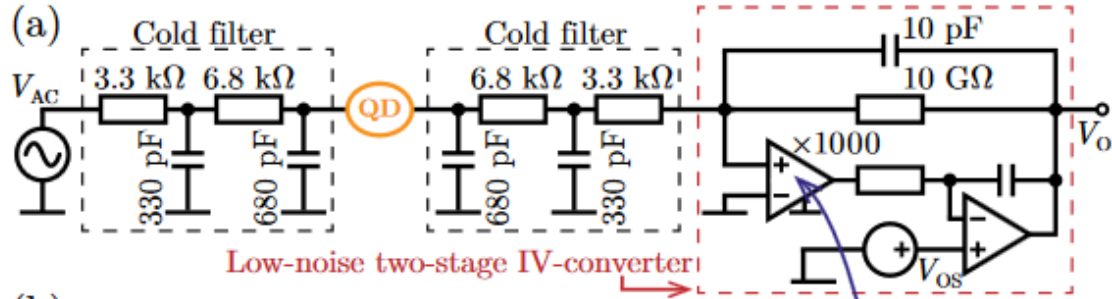
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## S2. Improve filtering. $T_e=11.2\text{mK}$ (Underwhelming step)

DAC output filter from 4ms to 22ms

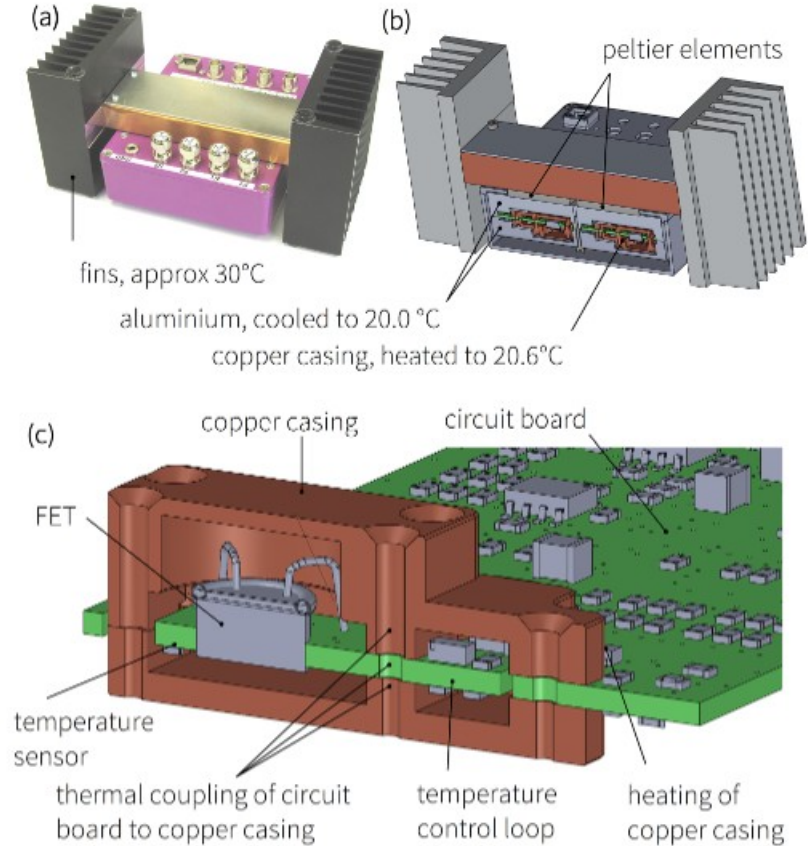
It's important to keep  $V_0$  constant

### S3. Replace IV Converter. $T_e = 9.49\text{mK}$

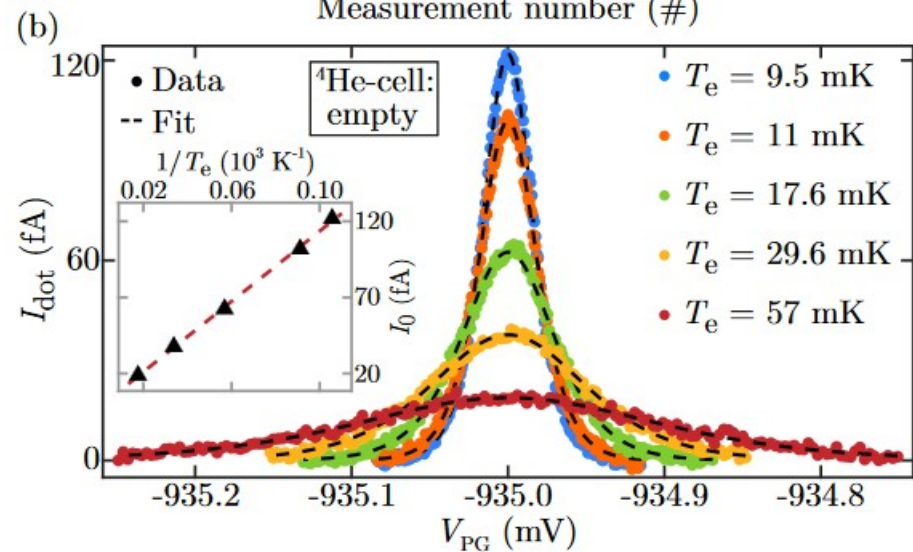
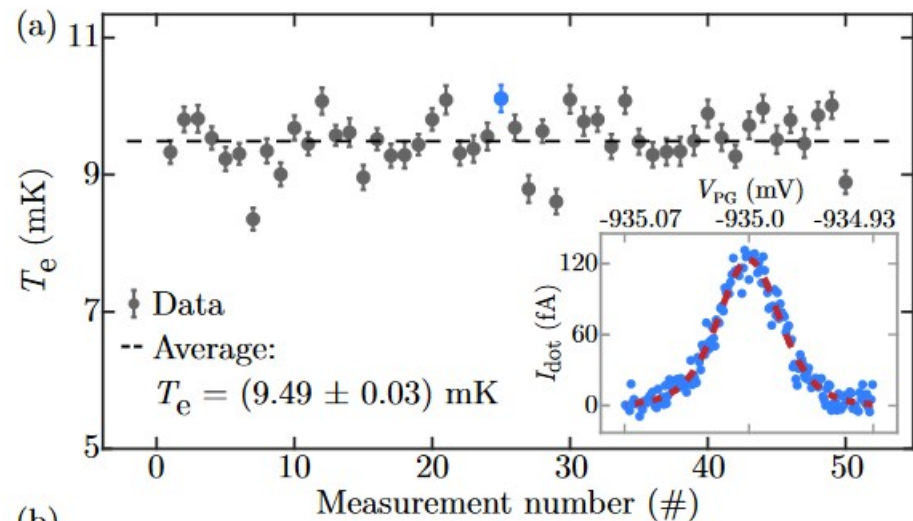


Johnson noise of  $1\text{M}\Omega$  is  $1\text{nV}/\sqrt{\text{Hz}}$  @  $10\text{mK}$

### Thermal stabilization



### S3. Replace IV Converter. $T_e = 9.49 \text{ mK}$



Fast measurements when  $1/f$  is present

Standard deviation vs. Standard error

$$\sigma = \sqrt{\frac{\sum_{i=1}^n (x_i - \bar{x})^2}{n - 1}}$$

$$(\sigma_{\bar{x}}) = \frac{\sigma}{\sqrt{n}}$$



S4. Fill the immersion cell.  $T_e = 8.20\text{mK}$

S5. Faster measurements.  $T_e = 7.45\text{mK}$

S6. Pulse-tube off.  $T_e = 6.74\text{mK}$

Imperfect thermalization at 40mK

